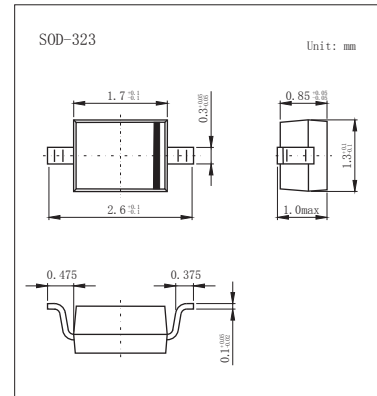


Schottky Diodes

BAT60B (KAT60B)

■ Features

- High Current Rectifier Schottky Diode with Low V_f Drop
- Low Voltage, Low Inductance
- For Power Supply
- For Detection and Step-up-Conversion

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
DC Blocking Voltage	V_R	10	V
Forward Current	I_F	3	A
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	5	
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	286	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 1\text{ mA}$	10			V
Forward voltage	V_{F1}	$I_F = 100\text{ mA}$			0.38	
	V_{F2}	$I_F = 500\text{ mA}$			0.5	
	V_{F3}	$I_F = 1000\text{ mA}$			0.6	
Reverse voltage leakage current	I_{R1}	$V_R = 5\text{ V}$			15	μA
	I_{R2}	$V_R = 8\text{ V}$			25	
Capacitance between terminals	C_T	$V_R = 5\text{ V}, f = 1\text{ MHz}$		30		pF

■ Marking

Marking	SL
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■ Typical Characteristics

